



DMT3020LFVW

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
30V	17mΩ @ V _{GS} = 10V	38A		
30 V	28mΩ @ V _{GS} = 4.5V	JOA		

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch

PowerDI3333-8 (SWP) (Type UX)

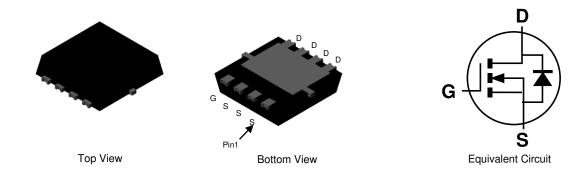
30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (SWP) (Type UX)

Features

- Low R_{DS(ON)} Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8
 Enabling Smaller End Product
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8 (SWP) (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)



Ordering Information (Note 4)

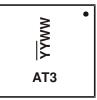
	Part Number	Case	Packaging		
	DMT3020LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2000/Tape & Reel		
	DMT3020LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3000/Tape & Reel		
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

No purposely added lead. Fully ED Directive 2002/95/EC (HOHS), 2017/65/ED (HOHS 2) & 2015/863/ED (HOHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} \underline{AT3} = Product Type Marking Code\\ \hline \underline{YY}WW = Date Code Marking\\ \hline \overline{YY} = Last Two Digits of Year (ex: 18 = 2018)\\ WW = Week Code (01 to 53) \end{array}$



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 7)	ID	38 30	А		
Maximum Body Diode Forward Current (Note 7)			Is	30	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	40	A
Pulsed Drain Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I _{SM}	40	A
Avalanche Current (L = 0.1mH) (Note 8)			IAS	13	А
Avalanche Energy (L = 0.1mH) (Note 8)			E _{AS}	8.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	124	°C/W
Total Power Dissipation (Note 6)		PD	2.0	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{0JC}	4.0	-C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	Oymbol	IVIIII	тур	Max	Onit		
Drain-Source Breakdown Voltage	BV _{DSS}	30.0		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	_	_	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	000						
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			12.5	17		$V_{GS} = 10V, I_D = 9.0A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	20.5	28	mΩ	$V_{GS} = 4.5V, I_D = 7.0A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 9)						· · ·	
Input Capacitance	C _{iss}		393	—	pF		
Output Capacitance	Coss		173	—	pF	− V _{DS} = 15V, V _{GS} = 0V, − f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		27	—	pF	1 - 1.000112	
Gate Resistance	Rg	_	1.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	
Total Gate Charge (V _{GS} = 10V)	Qg	—	7.0	—	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	3.6	—	nC		
Gate-Source Charge	Q _{gs}	_	0.9	—	nC	$V_{DD} = 15V, I_D = 9A$	
Gate-Drain Charge	Q _{qd}	_	1.5	—	nC		
Turn-On Delay Time	t _{D(ON)}		1.8	—	ns		
Turn-On Rise Time	t _R	_	1.9	—	ns		
Turn-Off Delay Time	t _{D(OFF)}		7.5	—	ns	$R_G = 6\Omega, I_D = 9A$	
Turn-Off Fall Time	tF		2.4	—	ns	7	
Reverse Recovery Time	t _{RR}		10	—	ns		
Reverse Recovery Charge	Q _{RR}	_	2.6	—	nC	I _F = 9A, dl/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.





[j **= 85°**℃

3.5

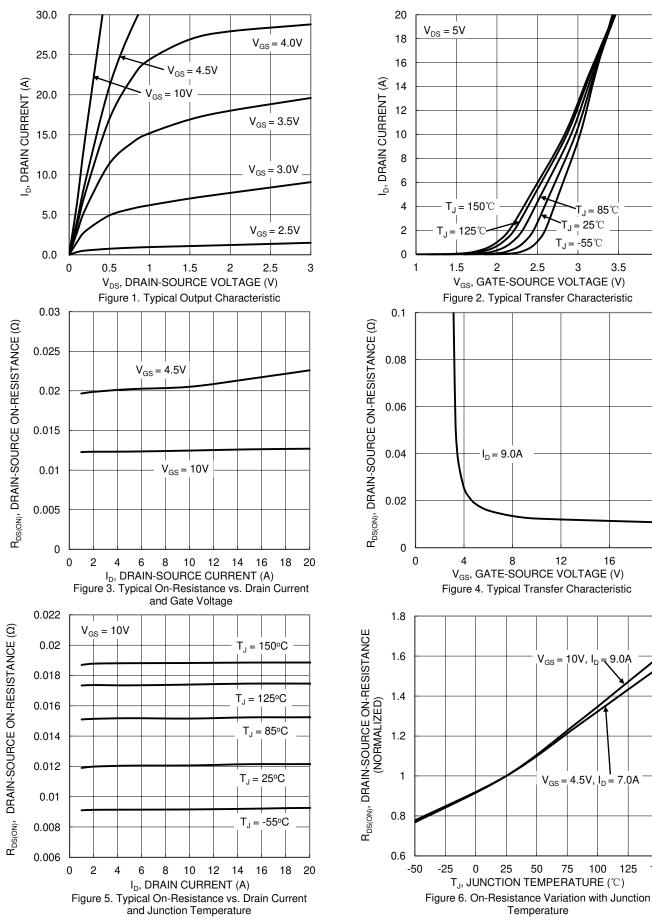
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20

4

= 25°C

3

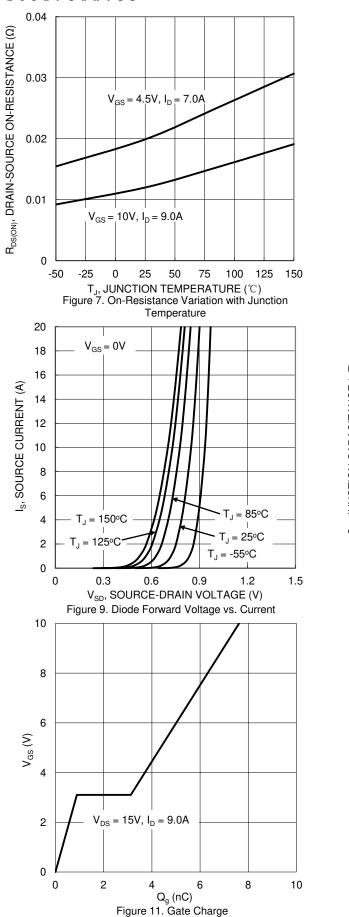


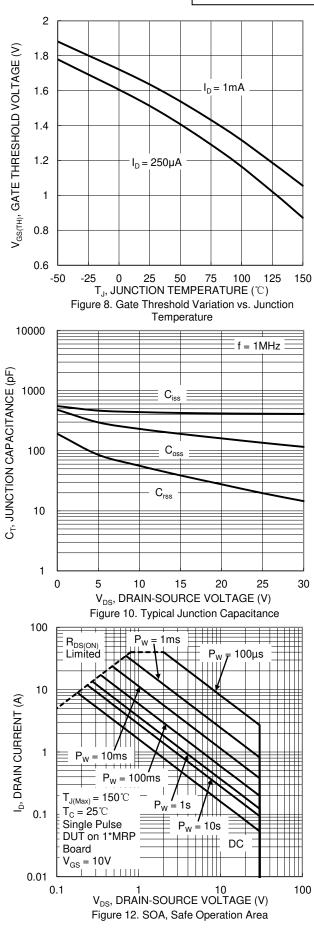
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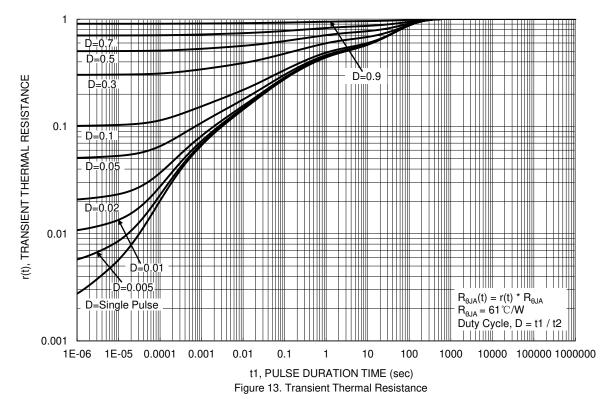










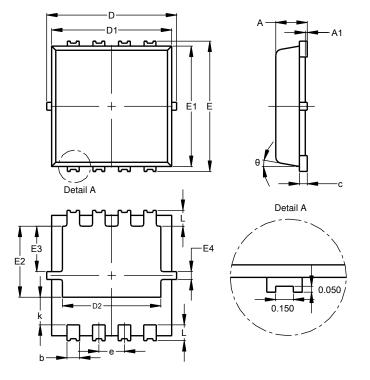




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

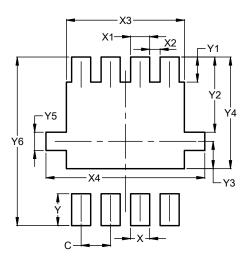


PowerDI3333-8 (SWP)						
(Type UX) Dim Min Max Typ						
Dim	Dim Min Max					
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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